



Express Mail No. EVA 074 517 826 US 05-223

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of: Thierry Barge et al.

Application No.: 10/069,058

Group Art Unit:

Filed: February 20, 2003

Examiner:

For: METHOD FOR TREATING SUBSTRATES
FOR MICROELECTRONICS AND
SUBSTRATES OBTAINED ACCORDING TO
SAID METHOD

Attorney Docket No.: 4717-4600

INFORMATION DISCLOSURE STATEMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Pursuant to their obligations under 35 U.S.C. 1.56, applicants submit herewith (21) references for the Examiner's review and consideration. These references are listed on a PTO form 1449, a copy of which is also enclosed. A copy of the international search report for the corresponding PCT application is also enclosed. Applicants respectfully request that these references be made of record in this application by the Examiner's completion and return of the PTO form 1449.

No fee is believed to be due for the filing of this statement. Should any fees be required, please charge such fees to Winston & Strawn Deposit Account No. 501-814.

Respectfully submitted,

Date: 3-25-03


Allan A. Fanucci 30,256
Reg. No.

**WINSTON & STRAWN
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Enclosures

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MAR 25 2003
PATENT & TRADEMARK OFFICE
LIST OF REFERENCES CITED BY APPLICANT
(Use several sheets if necessary)

ATTY. DOCKET NO.:	APPLICATION NO.:
4717-4600	10/069,058
APPLICANT:	
Thierry Barge et al.	

FILING DATE:	GROUP:
February 20, 2002	

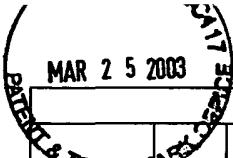
U.S. PATENT DOCUMENTS

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	AA	5,589,422	12/1996	Bhat	437	228	
	AB	5,374,564	12/1994	Bruel	437	24	
	AC	6,020,252	2/2000	Aspar et al.	438	458	
	AD	6,403,450 B1	6/2002	Maleville et al.	438	471	
	AE	6,429,104	8/2002	Auberton-Herve	438	527	

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	AF	EP 0 553 852 A	08/1993	Europe			X	
	AG	EP 0 917 193 A	05/1999	Europe			X	
	AH	EP 0 917 188 A	05/1999	Europe			X	
	AI	FR 2 681 472 A	03/1993	France - (US equivalent 5,374,564)			X	
	AJ	FR 2 777 115 A	10/1999	France - (US equivalent 6,403,450)			X	
	AK	FR 2 774 510 A	08/1999	France - (US equivalent 6,429,104)			X	
	AL	FR 2 761 526 A (US equivalent in English)	10/1998	France - (DE19753494 Abstract in English)			X	
	AM	FR 2 762 136 (with English Abstract)	10/1998	France - (DE19753494 Abstract in English)			X	
	AN	FR 2 761 526 (with English Abstract)	10/1998	France			X	
	AO	FR 2 748 851 A	11/1997	France - (US equivalent 6,020,252)			X	
	AO	DE 197 53494 English Abstract	10/1998	Germany			X	
	AP	JP 10242154 (with English Abstract)	09/1998	Japan			X	

MAR 25 2003



FOREIGN PATENT DOCUMENTS (cont....)

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	AQ	JP 5217821 English Abstract	08/1993	Japan			X	
	AR							

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

	AS	Moriceau, H., et al., "Hydrogen Annealing Treatment Used to Obtain High Quality SOI Surfaces," <u>Annual IEEE International Silicon-on-insulator Conference</u> , Vol. Conf. 24, pp. 37-38, New York (1998).
	AT	Maszara, W.P., et al., "Quality of SOI Film After Surface Smoothing With Hydrogen Annealing, Touch Polishing," <u>Proceedings of the 1997 IEEE International SOI Conference</u> , pp. 130-131, New York (1997).
	AU	Sato, N., et al., "Hydrogen Annealed Silicon-on-insulator," <u>Applied Physics Letters</u> , Vol. 65, No. 15, pp. 1924-1926, New York (1994).

EXAMINER	DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.